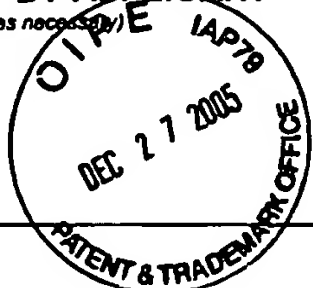


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Application Number 08/902,133

Filing Date July 29, 1997

First Named Inventor Forbes, Leonard

Group Art Unit 2815

Examiner Name

~~Eckert H, George~~ A. Wilson

Sheet 1 of 1

Attorney Docket No: 303.356US1

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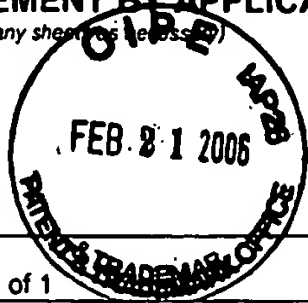
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Application Number	08/902,133
Filing Date	July 29, 1997
First Named Inventor	Forbes, Leonard
Group Art Unit	2815
Examiner Name	Wilson, Allan

Sheet 1 of 1

Attorney Docket No: 303.356US1

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Applicant: Leonard Forbes et al.

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Group: ~~2503~~ 2815

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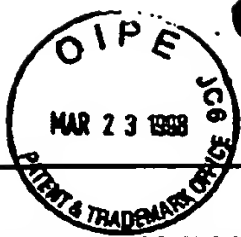
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Group: 2503 2815

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Form 1449\*

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Applicant: Leonard Forbes et al.

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Group: 2503-2815

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Examiner

v. markis wallace

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Form 1449\*

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INFORMATION DISCLOSURE STATEMENT  
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Applicant: Leonard Forbes et al.

Filing Date: July 29, 1997

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Examiner

V. Markie Waller

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3/3/99

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Sheet 5 of 7

Form 1449\*

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INFORMATION DISCLOSURE STATEMENT  
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Applicant: Leonard Forbes et al.

Filing Date: July 29, 1997

Group: 2505-2815

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Form 1449\*

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Filing Date: July 29, 1997

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V. Martin Wallace

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Form 1449\*

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Applicant: Leonard Forbes et al.

Filing Date: July 29, 1997

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Initial

(Including Author, Title, Date, Pertinent Pages, Etc.)

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V. Martin Walker

Date Considered

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